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SANYO SEMICONDUCTOR 2SD993

2SD993 NPN Triple Diffused Mesa Type Silicon Transistor
For H-Deflection Output (With Damper Diode)

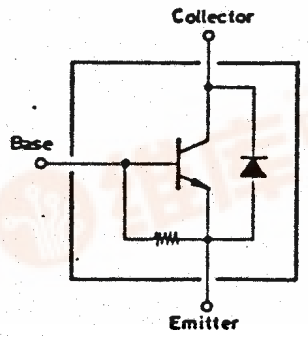
Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V_{CBO}		1500	V
Collector to Emitter Voltage	V_{CEO}		600	V
Emitter to Base Voltage	V_{EBO}		6	V
Collector Current	I_C		3	A
Collector Current (peak)	i_{cp}		6	A
Collector Dissipation	P_C		3	W
	P_C	Tc=25°C	50	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-40~+150	°C

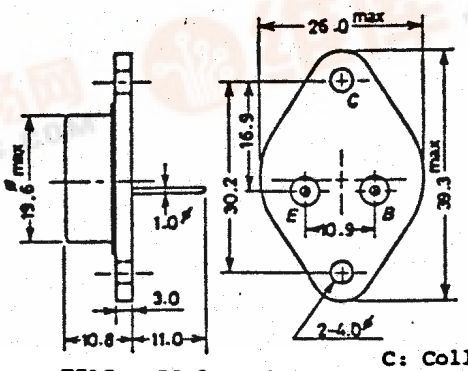
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cut off Current	I_{CES}	V_{CB}=1500V, V_{EB}=0			1.0	mA
Emitter Cut off Current	I_{EBO}	V_{BE}=4V, I_C=0	44		133	mA
Emitter to Base Voltage	V_{EBO}	I_E=200mA, I_C=0	6.0			V
Emitter to Collector Voltage	V_{ECO}	IE=2A, I_B=0			2.0	V
DC Current Gain	hFE	V_{CE}=5V, I_C=2A	3		15	
C-E Saturation Voltage	V_{CE}(sat)	I_C=2.5, I_B=0.6A			10	V
B-E Saturation Voltage	V_{BE}(sat)	I_C=2.5, I_B=0.6A			1.3	V
C-E sustain Voltage	V_{CE}(sus)	I_C=100mA, I_B=0, L=35mH	600			V
Fall Time	t_f	I_C=2.5A, I_B=0.5A, t=10 90% Tc=80°C			1.0	μs

Equivalent Circuit



Case Outline (unit:mm)



EIAJ: TC-3, TB-3
JEDEC: TO-3

C: Collector
E: Emitter
B: Base

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